

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ~~manufacturing~~-method for manufacturing a substrate used for a liquid crystal device by slant vacuum deposition ~~oblique evaporation~~ of an inorganic material on an underlayer having a gap section on ~~the surface~~a surface formed on the substrate so as to ~~form the~~form an inorganic alignment layers, ~~comprising the steps of~~layer, comprising:

a first oblique evaporation step by unidirectional oblique evaporation of slant vacuum deposition step of disposing the inorganic material unidirectionally on the substrate on which the underlayer having the gap section is formed on the surface of formed on the substrate so as to form the first a first inorganic oblique evaporation layer 36a; slant vacuum deposition layer;

a second oblique evaporation slant vacuum deposition step by oblique evaporation of disposing the inorganic material on the substrate unidirectionally, a direction in the second slant vacuum deposition step having an from at least a different azimuth angle inside the substrate from the oblique evaporation direction of the inorganic material in the first oblique evaporation step different from at least an azimuth angle of the first slant vacuum deposition step so as to form the second oblique evaporation layer 36b in an area close to a second inorganic slant vacuum deposition layer near the gap section and on the first inorganic oblique evaporation layer slant vacuum deposition layer, wherein the direction for disposing the inorganic material unidirectionally in the first or the second slant vacuum deposition step is along a longitudinal direction of the gap section.

2. (Currently Amended) ~~A manufacturing~~The method for manufacturing a substrate the substrate used for a the liquid crystal device,device according to claim 1, wherein

the azimuth angle of the oblique evaporation direction (S_A) of the inorganic material in first slant vacuum deposition the first oblique evaporation step and the azimuth angle of the oblique evaporation direction (S_B) of the inorganic material in the second oblique evaporation step differs slant vacuum deposition step differing by nearly 90 degrees.

3. (Currently Amended) A manufacturing The method of a substrate manufacturing the substrate used for a the liquid crystal device according to claim 1, wherein:

deposition a deposition angle (θ_1) between the oblique evaporation direction of the for disposing the inorganic material in the first oblique evaporation slant vacuum deposition step and the substrate is in being in the range of 5 to 10 degrees;

deposition a deposition angle (θ_2) between the oblique evaporation direction of the for disposing the inorganic material in the second oblique evaporation slant vacuum deposition step and the substrate is in being in the range of 25 to 30 degrees.

4. (Currently Amended) A manufacturing The method for a of manufacturing the substrate used for a the liquid crystal device,device according to claim 1, wherein the a slant vacuum deposition oblique evaporation direction (S_A, S_B) is being selected according to a construction and disposition of the gap section (80)section formed on the surfacea surface of the underlayer in the oblique evaporation of inorganic material in at least one of the first oblique evaporationslant vacuum deposition step and the second oblique evaporationslant vacuum deposition step.

5. (Currently Amended) A manufacturing The method of manufacturing for a the substrate used for a the liquid crystal device,device according to claim 1, wherein:

the thickness of the inorganic the first inorganic slant vacuum deposition oblique evaporation layer formed in the first oblique evaporationslant vacuum deposition step is in the range of 5 nm to 16 nm; and

the thickness of the second inorganic slant vacuum deposition ~~the inorganic oblique evaporation~~ layer formed in the second ~~oblique evaporation~~ slant vacuum deposition step is in the range of 10 nm to 40 nm.

6. (Currently Amended) ~~A manufacturing~~ The method for a substrate of manufacturing the substrate used for a ~~the~~ liquid crystal device, device according to claim 1, ~~wherein~~ the inorganic material is silicon being silicon oxide.